

CLAIM AMENDMENTS

1. (Currently Amended) An integrated circuit device comprising:
a semiconductor amplification element supplied with a voltage from a first power source; and
a bias circuit for applying a bias voltage to the semiconductor amplification element,
wherein
~~a power source of the bias circuit is supplied with a second voltage from a~~
second power source,
~~the second power source is connected to a the first power source of the~~
~~semiconductor amplification element via a semiconductor element such that, and~~
idle current of the semiconductor amplification element ~~is changed~~ changes in
response to a change of a supply the voltage of supplied by the first power source to the
semiconductor amplification element.
2. (Previously Presented) The integrated circuit device according to Claim 1, wherein
the semiconductor element is a transistor.
3. (Previously Presented) The integrated circuit device according to Claim 1, wherein
the semiconductor element is a diode.
4. (Currently Amended) The integrated circuit device according to Claim 1, which acts
as a power amplifier circuit, including a transistor as the semiconductor amplification element,
wherein the bias circuit includes a bias generating circuit for generating a base bias of the
transistor and a temperature compensation circuit for temperature compensation of the bias
generating circuit.